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➤ BRS:
➤ BRS:
➤ BRS:
➤ BRS: (Moat$3 adj gate) same (control adj gate)
➤ BRS:
➤ BRS:
➤ Pending
➤ Active
➤ 11: (16) 08/945496
➤ 12: (16) 08/943194
➤ 13: (16) 08/945507
➤ 14: (16) 08/945512
➤ 15: (16) 08/945554
➤ 16: (23) 12 3 4 5
➤ 17: (1248) (l(asy)mmetr($4 graded) near 2 (moat
➤ 18: (16) (l(asy)mmetr($4 graded) near 2 (tunnel)$
➤ 19: (162288) tunnel$4 intergate inter adj gate
➤ 110: (26) 7 with 0
➤ 111: (28) 0 10
➤ 112: (16) 11 not 0

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11 not 8

03/31/2005

	U	1	Inventor	Document ID	Issue Date	Page	Title	Current BR	Current IRe
1			AHN, KY et al.	US 20050023595 A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrical fo		
2			AHN, KY et al.	US 20050023603 A	20050203	32	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate that is separated from floating gate by asymmetrical fo		
3			AHN, KY et al.	US 20050023602 A	20050203	37	Flash memory array for personal computers, digital cameras, or wireless phones, has control gate separated from floating gate by asymmetrical low turn		
4			AHN, KY et al.	US 20030040666 A	20030313	39	Floating gate transistor for memory array used in programmable logic array, comprises control gate opposing floating gate, and is separated from floating ga		
5			AHN, KY et al.	US 20030042527 A	20030306	38	Depletion mode floating gate transistor for flash memory, has control gate separated from floating gate by asymmetrical metal oxide made low tunnel barri		
6			CHEN, Y et al.	CN 1527099 A	20040908	NA	Setting method and device for surface ion body induced photon resonance tunnelling type one-dimensional photonic band gap structure		
7			Higuroshi, Hitoshi	US 5648559 A	19970708	24	Single-electron tunnelling logic device	326/136	257/31; 257/E26.322
8			MARKS, A M	EP 172464 A	19960226	33	Femto diode and applications - has sub-micron metal cylinder with asymmetric tunnel junction and reflecting stag		
9			Marks: Aaron M.	US 5268256 A	19931207	13	Monomolecular resist and process for beamwriter	430/296	
10			Marks: Aaron M.	US 4872094 A	19901120	15	Lighting devices with quantum electric/light power converters	307/150	257/88; 257/E26.02